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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Complete if Known	
		Application Number	
		Filing Date	August 20, 2003
		First Named Inventor	Viktor Koldiaev
		Group Art Unit	
Examiner Name			
Attorney Docket Number	88103.0001		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		Chin-hsing Yu, et al., Ultrathin (2.7nm) Oxy-nitride for Suppressing Boron Penetration Characterized by Direct Hole Tunneling Current in p+/pMOS, Technology Development Center, Worldwide Semiconductor Manufacturing Corp., Hsinchu, Taiwan 30077, Republic of China	
		S.C. Song, et al., Ultra Thin high quality stack nitride/oxide gate dielectrics prepared by <i>in-situ</i> rapid thermal N ₂ O oxidation of NH ₃ -nitrided Si, Microelectronics Research Center, Department of Electrical and Computer Engineering The University of Texas, Austin, TX	
		Quazi D. M., Khosru, et al., Low Thermal-Budget Ultrathin NH ₃ -Annealed Atomic-Layer-Deposited Si-Nitride/SiO ₂ Stack Gate Dielectrics With Excellent Reliability, IEEE Electron Device Letters, Vol. 23, No. 4, April 2002	
		Quazi D.M., Khosru, et al., Ultrathin NH ₃ Annealed Atomic Layer Deposited Si-nitride/SiO ₂ Stack Gate Dielectrics with High Reliability, Research Centr for Nanodevices and Systems, Hiroshima University, 1-4-2 Kagamiyama, Higashi-Hiroshima, Japan	

Examiner Signature	J. MONDT	Date Considered	10/14/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

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